Physics Of Low Dimensional Semiconductors Solutions Manual

This book combines new physics and the latest device developments in low dimensional semiconductors. The development and application of low dimensional semiconductors has been rapid and spectacular during the past decade. Ever improving epitaxial growth and device fabrication techniques have allowed access to some remarkable new physics in quantum confined structures, while in parallel, a plethora of new devices have emerged. The field of optoelectronics in particular has benefited from these advances both in terms of improved performance and the invention of fundamentally new types of device, at a time when the use of optics and lasers in telecommunications, broadcasting, the internet, signal processing and computing has been rapidly expanding. An appreciation of the physics of quantum and dynamical electronic processes in confined structures in key to the understanding of many of the latest devices and involvement in their continued development. This book allows those who already have somefamiliarity with semiconductor physics and devices, to broaden and expand their knowledge into new and expanding topics in low dimensional semic
The author develops the effective-mass theory of excitons in low-dimensional semiconductors and describes numerical methods for calculating the optical absorption including Coulomb interaction, geometry, and external fields. The theory is applied to Fano resonances in low-dimensional semiconductors and the Zener breakdown in superlattices. Comparing theoretical results with experiments, the book is essentially self-contained; it is a hands-on approach with detailed derivations, worked examples, illustrative figures, and computer programs. The book is clearly structured and will be valuable as an advanced-level self-study or course book for graduate students, lecturers, and researchers.
This volume contains a sequence of reviews presented at the NATO Advanced Study Institute on 'Low Dimensional Structures in Semiconductors ... from Basic Physics to Applications.' This was part of the International School of Materials Science and 1990 at the Ettore Majorana Centre in Sicily. Technology held in July Only a few years ago, Low Dimensional Structures was an esoteric concept, but now it is apparent they are likely to playa major role in the next generation of electronic devices. The theme of the School acknowledged this rapidly developing maturity.' The contributions to the volume consider not only the essential physics, but take a wider view of the topic, starting from material growth and processing, then prog ressing right through to applications with some discussion of the likely use of low dimensional devices in systems. The papers are arranged into four sections, the first of which deals with basic con cepts of semiconductor and low dimensional systems. The second section is on growth and fabrication, reviewing MBE and MOVPE methods and discussing the achievements and limitations of techniques to reduce structures into the realms of one and zero dimensions. The third section covers the crucial issue of

interfaces while the final section deals with devices and device physics.

When solids are reduced to the nanometer scale, they exibit new and exciting behaviours which constitute the basis for a new generation of electronic devices. Nanotechnology for Microelectronics and Optoelectronics outlines in detail the fundamental solid-state physics concepts that explain the new properties of matter caused by this reduction of solids to the nanometer scale. Applications of these electronic properties is also explored, helping students and researchers to appreciate the current status and future potential of nanotechnology as applied to the electronics industry. Explains the behavioural changes which occur in solids at the nanoscale, making them the basis of a new generation of electronic devices Laid out in text-reference style: a cohesive and specialised introduction to the fundamentals of nanoelectronics and nanophotonics for students and researchers alike

The Physics of Low-dimensional SemiconductorsAn IntroductionCambridge University Press

This book reviews up-to-date ideas of how the luminescence radiation in semiconductors originates and how to analyze it experimentally. The book fills a gap between general textbooks on optical properties of solids and specialized monographs on luminescence. It is unique in its coherent treatment of the phenomenon of luminescence from the very introductory definitions, from light emission in bulk crystalline and amorphous materials to the advanced chapters that deal with semiconductor nano objects, including spectroscopy of individual nanocrystals. The theory of radiative recombination channels in semiconductors is considered on a level of intuitive physical understanding rather than rigorous quantum mechanical treatment. The book is based on teaching and written in the style of a graduate text with plenty of tutorial material, illustrations, and problem sets at chapter ends. It is designed predominantly for students in physics, optics, optoelectronics and materials science.

Publisher Description

Designed to sit alongside more conventional established condensed matter physics textbooks, this compact volume offers a concise presentation of the principles of solid state theory, ideal for advanced students and researchers requiring an overview or a quick refresher on a specific topic. The book starts from the one-electron theory of solid state physics, moving through electron-electron interaction and many-body approximation schemes, to lattice oscillations and their interactions with electrons. Subsequent chapters discuss transport theory and optical properties, phase transitions and some properties of low-dimensional semiconductors. Throughout the text, mathematical proofs are often only sketched, and the final chapter of the book reviews some of the key concepts and formulae used in theoretical physics. Aimed primarily at graduate and advanced undergraduate students taking courses on condensed matter theory, the book serves as a study guide to reinforce concepts learned through conventional solid state texts. Researchers and lecturers will also find it a useful resource as a concise set of notes on fundamental topics.

This book offers, from both a theoretical and a computational perspective, an analysis of macroscopic mathematical models for description of charge transport in electronic devices, in particular in the presence of confining effects, such as in the double gate MOSFET. The models are derived from the semiclassical Boltzmann equation by means of the moment method and are closed by resorting to the maximum entropy principle. In the case of confinement, electrons are treated as waves in the confining direction by solving a one-dimensional Schrödinger equation obtaining subbands, while the longitudinal transport of subband electrons is described semiclassically. Limiting energy-transport and drift-diffusion models are also obtained by using suitable scaling procedures. An entire chapter in the book is dedicated to a promising new material like graphene. The models appear to be sound and sufficiently accurate for systematic use in computer-aided design simulators for complex electron devices. The book is addressed to applied mathematicians, physicists, and electronic engineers. It is written for graduate or PhD readers but the opening chapter contains a modicum of semiconductor physics, making it self-consistent and useful also for undergraduate students.

This textbook provides a theoretical background for contemporary trends in solid-state theory and semiconductor device physics. It discusses advanced methods of quantum mechanics and field theory and is therefore primarily intended for graduate students in theoretical and experimental physics who have already studied electrodynamics, statistical physics, and quantum mechanics. It also relates solid-state physics fundamentals to semiconductor device applications and includes auxiliary results from mathematics and quantum mechanics, making the book useful also for graduate students in electrical engineering and material science. Key Features: Explores concepts common in textbooks on semiconductors, in addition to topics not included in similar books currently available on the market, such as the topology of Hilbert space in crystals Contains the latest research and developments in the field Written in an accessible yet rigorous manner

This volume contains the Proceedings of the NATO Advanced Research Workshop on "Growth and Optical Properties of Wide Gap II-VI Low Dimensional Semiconductors", held from 2 - 6 August 1988 in Regensburg, Federal Republic of Germany, under the auspices of the NATO International Scientific Exchange Programme. Semiconducting compounds formed by combining an element from column II of the periodic table with an element from column VI (so called II-VI Semiconductors) have long promised many optoelectronic devices operating in the visible region of the spectrum. However, these materials have encountered numerous problems including: large number of defects and difficulties in obtaining p- and n-type doping. Advances in new methods of material preparation may hold the key to unlocking the unfulfilled promises. During the workshop a full session was taken up covering the prospects for wide-gap II-VI Semiconductor devices, particularly light emitting ones. The growth of bulk materials was reviewed with the view of considering II-VI substrates for the novel epitaxial techniques such as MOCVD, MBE, ALE, MOMBE and ALE-MBE. The controlled introduction of impurities during non-equilibrium growth to provide control of the doping type and conductivity was emphasized.

The discovery of the quantized and fractional Quantum Hall Effect phenomena is among the most important physics findings in the latter half of this century. The precise quantization of the electrical resistance involved in the quantized Hall effect phenomena has led to the new definition of the resistance standard and has metrologically affected all of science and technology. This resource consists of contributions from the top researchers in the field who present recent experimental and theoretical developments. Each chapter is self-contained and includes its own set of references guiding readers to original papers and further reading on the topic.

Starting with the first transistor in 1949, the world has experienced a technological revolution which has permeated most aspects of modern life, particularly over the last generation. Yet another such revolution looms up before us with the newly developed capability to control matter on the nanometer scale. A truly extraordinary research effort, by scientists, engineers, technologists of all disciplines, in nations large and small throughout the world, is directed and vigorously pressed to develop a full understanding of the properties of matter at the nanoscale and its possible applications, to bring to fruition the promise of nanostructures to introduce a new generation of electronic and optical devices. The physics of low dimensional semiconductor structures, including heterostructures, superlattices, quantum wells, wires and dots is reviewed and their modeling is discussed in detail. The truly exceptional material, Graphene, is reviewed; its functionalization and Van der Waals interactions are included here. Recent research on optical studies of quantum dots and on the physical properties of one-dimensional quantum wires is also reported. Chapters on fabrication of nanowire – based nanogap devices by the dielectrophoretic assembly approach. The broad spectrum of research reported here incorporates chapters on nanoengineering and nanophysics. In its presentation of tutorial chapters as well as advanced research on nanostructures, this book is ideally suited to meet the needs of newcomers to the field as well as experienced researchers interested in viewing colleagues' recent advances.

Quantum well devices have been the objects of intensive research during the last two decades. Some of the devices have matured into commercially useful products and form part of modern electronic circuits. Some others require further dev- opment, but have the promise of being useful commercially in the near future. Study of the devices is, therefore, gradually becoming compulsory for electronics specialists. The functioning of the devices, however, involve aspects of physics which are not dealt with in the available text books on the physics of semicond- tor devices. There is, therefore, a need for a book to cover all these

aspects at an introductory level. The present book has been written with the aim of meeting this need. In fact, the book grew out of introductory lectures given by the author to graduate students and researchers interested in this rapidly developing area of electron devices. The book covers the subjects of heterostructure growth techniques, band-offset theory and experiments, electron states, electron-photon interaction and related phenomena, electron transport and the operation of electronic, opto-electronic and photonic quantum well devices. The theory as well as the practical aspects of the devices are discussed at length. The aim of the book is to provide a comprehensive treatment of the physics underlying the various devices. A reader after going through the book should find himself equipped to deal with all kinds of quantum well devices.
Defects in Advanced Electronic Materials and Novel Low Dimensional Structures provides a comprehensive review on the recent progress in solving defect issues and deliberate defect engineering in novel material systems. It begins with an overview of point defects in ZnO and group-III nitrides, including irradiation-induced defects, and then look at defects in one and two-dimensional materials, including carbon nanotubes and graphene. Next, it examines the ways that defects can expand the potential applications of semiconductors, such as energy upconversion and quantum processing. The book concludes with a look at the latest advances in theory. While defect physics is extensively reviewed for conventional bulk semiconductors, the same is far from being true for novel material systems, such as low-dimensional 1D and 0D nanostructures and 2D monolayers. This book fills that necessary gap. Presents an in-depth overview of both conventional bulk semiconductors and low-dimensional, novel material systems, such as 1D structures and 2D monolayers Addresses a range of defects in a variety of systems, providing a comparative approach Includes sections on advances in theory that provide insights on where this body of research might lead

Experimental progress over the past few years has made it possible to test a n- ber of fundamental physical concepts related to the motion of electrons in low dimensions. The production and experimental control of novel structures with typical sizes in the sub-micrometer regime has now become possible. In parti- lar, semiconductors are widely used in order to con?ne the motion of electrons in two-dimensional heterostructures. The quantum Hall e?ect was one of the ?rst highlights of the new physics that is revealed by this con?nement. In a further step of the technological development in semiconductor-heterostructures, other arti?cial devices such as quasi one-dimensional ‘quantum wires’ and ‘quantum dots’ (arti?cial atoms) have also been produced. These structures again di?er very markedly from three- and two-dimensional systems, especially in relation to the transport of electrons and the interaction with light. Although the technol- ical advances and the experimental skills connected with these new structures are progressing extremely fast, our theoretical understanding of the physical e?ects (such as the quantum Hall e?ect) is still at a very rudimentary level. In low-

dimensional structures, the interaction of electrons with one another and with other degrees of freedoms such as lattice vibrations or light gives rise to new phenomena that are very di?erent from those familiar in the bulk ma- rial. The theoretical formulation of the electronic transport properties of small devices may be considered well-established, provided interaction processes are neglected.
Here is a discussion of the state of the art of spin resonance in low dimensional structures, such as two-dimensional electron systems, quantum wires, and quantum dots. Leading scientists report on recent advances and discuss open issues and perspectives.
The optical properties of semiconductors have played an important role since the identification of semiconductors as "small" bandgap materials in the thinies, due both to their fundamental interest as a class of solids baving specific optical propenies and to their many important applications. On the former aspect we can cite the fundamental edge absorption and its assignment to direct or indirect transitions, many-body effects as revealed by exciton formation and photoconductivity. On the latter aspect, large-scale applications sucb as LEDs and lasers, photovoltaic converters, photodetectors, electro-optics and non-linear optic devices, come to mind. The eighties saw a revitalization of the whole field due to the advent of heterostructures of lower-dimensionality, mainly two-dimensional quantum wells, which through their enhanced photon-matter interaction yielded new devices with unsurpassed performance. Although many of the basic phenomena were evidenced through the seventies, it was this impact on applications which in turn led to such a massive investment in fabrication tools, thanks to which many new structures and materials were studied, yielding funher advances in fundamental physics.
This book surveys recent experimental and theoretical studies on optical properties of low-dimensional materials, e.g., artificial crystals in zeolites, C60 and its related compounds, silicon nanostructures including porous Si, II-VI and III-V semiconductor quantum structures, and Pb-based natural quantum-well systems. The eight excellent detailed review articles are written by authorities on each field in Japan. All the materials introduced in this book yield new optical phenomena originating from their mesoscopic and low-dimensional characters contributing to a new research field of condensed matter and optical physics. Contents:Dimensionality and Optical Responses of Materials (T Ogawa)Ab initio Calculation of Nonlinear Optical Susceptibility (T Nakayama)Wannier-Stark Localization in Semiconductor Superlattices (M Nakayama)Ultraviolet Laser Emission from ZnS-Based Quantum Wells (Y Yamada)Luminescence from Silicon Nanostructures (Y Kanemitsu)Optical Properties of Pb-Based Inorganic-Organic Perovskites (T Ishihara)Solid State Properties of C60 and Its Related Materials (Y Iwasa)Arrayed Nanoclusters in Zeolite Crystals (Y Nozue) Readership: Researchers in materials science, nanoscience, optics, semiconductors, condensed matter physics and applied physics. keywords:Low Dimension;Optical Property;Materials Science;Nanoscience;Quantum Confinement;Exciton;Phonon;Photon;Electronic Structure;Lattice Structure
Semiconductors are at the heart of modern living. Almost everything we do, be it work, travel, communication, or entertainment, all depend on some feature of semiconductor technology. Comprehensive Semiconductor Science and Technology captures the breadth of this important field, and presents it in a single source to the large audience

who study, make, and exploit semiconductors. Previous attempts at this achievement have been abbreviated, and have omitted important topics. Written and Edited by a truly international team of experts, this work delivers an objective yet cohesive global review of the semiconductor world. The work is divided into three sections. The first section is concerned with the fundamental physics of semiconductors, showing how the electronic features and the lattice dynamics change drastically when systems vary from bulk to a low-dimensional structure and further to a nanometer size. Throughout this section there is an emphasis on the full understanding of the underlying physics. The second section deals largely with the transformation of the conceptual framework of solid state physics into devices and systems which require the growth of extremely high purity, nearly defect-free bulk and epitaxial materials. The last section is devoted to exploitation of the knowledge described in the previous sections to highlight the spectrum of devices we see all around us. Provides a comprehensive global picture of the semiconductor world Each of the work's three sections presents a complete description of one aspect of the whole Written and Edited by a truly international team of experts

This book deals with the Effective Electron Mass (EEM) in low dimensional semiconductors. The materials considered are quantum confined non-linear optical, III-V, II-VI, GaP, Ge, PtSb2, zero-gap, stressed, Bismuth, carbon nanotubes, GaSb, IV-VI, Te, II-V, Bi2Te3, Sb, III-V, II-VI, IV-VI semiconductors and quantized III-V, II-VI, IV-VI and HgTe/CdTe superlattices with graded interfaces and effective mass superlattices. The presence of intense electric field and the light waves change the band structure of optoelectronic semiconductors in fundamental ways, which have also been incorporated in the study of the EEM in quantized structures of optoelectronic compounds that control the studies of the quantum effect devices under strong fields. The importance of measurement of band gap in optoelectronic materials under strong electric field and external photo excitation has also been discussed in this context. The influence of crossed electric and quantizing magnetic fields on the EEM and the EEM in heavily doped semiconductors and their nanostructures is discussed. This book contains 200 open research problems which form the integral part of the text and are useful for both Ph. D aspirants and researchers in the fields of solid-state sciences, materials science, nanoscience and technology and allied fields in addition to the graduate courses in modern semiconductor nanostructures. The book is written for post graduate students, researchers and engineers, professionals in the fields of solid state sciences, materials science, nanoscience and technology, nanostructured materials and condensed matter physics.

This book is a comprehensive text on the physics of semiconductors and nanostructures for a large spectrum of students at the final undergraduate level studying physics, material science and electronics engineering. It offers introductory and advanced courses on solid state and semiconductor physics on one hand and the physics of low dimensional semiconductor structures on the other in a single text book. Key Features Presents basic concepts of quantum theory, solid state physics, semiconductors, and quantum nanostructures such as quantum well, quantum wire, quantum dot and superlattice In depth description of semiconductor heterojunctions, lattice strain and modulation doping technique Covers transport in nanostructures under an electric and magnetic field with the topics: quantized conductance, Coulomb blockade, and integer and fractional quantum Hall effect Presents the optical processes in nanostructures under a magnetic field Includes illustrative problems with hints for solutions in each chapter Physics of Semiconductors and Nanostructures will be helpful to students initiating PhD work in the field of semiconductor nanostructures and devices. It follows a unique tutorial approach meeting the requirements of students who find learning the concepts difficult and want to study from a physical perspective.

Low-Dimensional Semiconductor Structures provides a seamless, atoms-to-devices introduction to the latest quantum heterostructures. It covers their fabrication, their electronic, optical, and transport properties, their role in exploring new physical phenomena, and their utilization in devices. The authors begin with a detailed description of the epitaxial growth of semiconductors. They then deal with the physical behaviour of electrons and phonons in low-dimensional structures. A discussion of localization effects and quantum transport phenomena is followed by coverage of the optical properties of quantum wells. They then go on to discuss nonlinear optics in quantum heterostructures. The final chapters deal with semiconductor lasers, mesoscopic devices, and high-speed heterostructure devices. The book contains many exercises and comprehensive references. It is suitable as a textbook for graduate-level courses in electrical engineering and applied physics. It will also be of interest to engineers involved in the development of new semiconductor devices.

Beginning graduate introduction to low-dimensional systems and their applications.

Theoretical and experimental work on solids with low-dimensi onal cooperative phenomena has been rather explosively expanded in the last few years, and it seems to be quite fashionable to con tribute to this field, especially to the problem of one-dimensional metals. On the whole, one could divide the huge amount of recent investigations into two parts although there is much overlap bet ween these regimes, namely investigations on magnetic exchange interactions constrained to mainly one or two dimensions and, secondly, work done on Id metallic solids or linear chain compounds with Id delocalized electrons. There is, of course, overlap from one extreme case to the other with these solids and in some rare cases both phenomena are studied on one and the same crystal. In fact, however, most of the scientific groups in this area could be associated roughly with one of these categories and,in addition, a separation between theoreticians and experimentalists in each of these groups leads to a further splitting of interests although many theories about these solids have been tested by experimenta lists. Nevertheless, more cooperation and understanding between scientists working on low-dimensional cooperative phenomena should appreciably stimulate further development. With a better inderdis ciplinary understanding, new ideas could possibly help chemists in synthesizing tailor-cut solids. This would in return give experi mentalists new phenomena to examine and finally would stimulate new theoretical work.

Presenting the latest advances in artificial structures, this volume discusses in-depth the structure and electron transport mechanisms of quantum wells, superlattices, quantum wires, and quantum dots. It will serve as an invaluable reference and review for researchers and graduate students in solid-state physics, materials science, and electrical and electronic engineering.

The development and application of low-dimensional semiconductors have been rapid and spectacular during the past decade. Ever improving epitaxial growth and device fabrication techniques have allowed access to some remarkable new physics in quantum confined structures while a plethora of new devices has emerged. The field of optoelectronics in particular has benefited from these advances both in terms of improved performance and the invention of fundamentally new types of device, at a time when the use of optics and lasers in telecommunications, broadcasting, the Internet, signal processing, and computing has been rapidly expanding. An appreciation of the physics of quantum and dynamic electronic processes in confined structures is key to the understanding of many of the latest devices and their continued development. Semiconductor Quantum Optoelectronics covers new physics and the latest device developments in low-dimensional semiconductors. It allows those who already have some familiarity with semiconductor physics and devices to broaden and expand their knowledge into new and expanding topics in low-dimensional semiconductors. The book provides pedagogical coverage of selected areas of new and pertinent physics of low-dimensional structures and presents some optoelectronic devices presently under development. Coverage includes material and band structure issues and the physics of ultrafast, nonlinear, coherent, intersubband, and intracavity phenomena. The book emphasizes various devices, including quantum wells, visible, quantum cascade, and mode-locked lasers; microcavity LEDs and VCSELs; and detectors and logic elements. An underlying theme is high-speed phenomena and devices for increased system bandwidths.

Modern Semiconductor Quantum Physics has the following constituents: (1) energy band theory: pseudopotential method (empirical and ab initio); density functional theory; quasi-particles; LCAO method; k.p method; spin-orbit splitting; effect mass and Luttinger parameters; strain effects and deformation potentials; temperature effects. (2) Optical properties: absorption and exciton effect; modulation spectroscopy; photo luminescence and photo luminescence excitation; Raman scattering and polaritons; photoionization. (3) Defects and Impurities: effective mass theory and shallow impurity states; deep state cluster method, super cell method, Green's function method; carrier recombination kinetics; trapping transient measurements; electron spin resonance; electron lattice interaction and lattice relaxation effects; multi-phonon nonradiative recombination; negative U center, DX center and EL2 Defects. (4) Semiconductor surfaces: two dimensional periodicity and surface reconstruction; surface electronic states; photo-electron spectroscopy; LEED, STM and other experimental methods. (5) Low-dimensional structures: Heterojunctions, quantum wells; superlattices, quantum-confined Stark effect and Wannier-Stark ladder effects; resonant tunneling, quantum Hall effect, quantum wires and quantum dots.This book can be used as an advanced textbook on semiconductor physics for graduate students in physics and electrical engineering departments. It is also useful as a research reference for solid state scientists and semiconductor device engineers.

A recent major development in high technology, and one which bears considerable industrial potential, is the advent of low-dimensional semiconductor quantum structures. The research and development activity in this field is moving fast and it is thus important to afford scientists and engineers the opportunity to get updated by the best experts in the field. The present book draws together the latest developments in the fabrication technology of quantum structures, as well as a competent and extensive review of their fundamental properties and some remarkable applications. The book is based on a set of lectures that introduce different aspects of the basic knowledge available, it has a tutorial content and could be used as a textbook. Each aspect is reviewed, from elementary concepts up to the latest developments. Audience: Undergraduates and graduates in electrical engineering and physics schools. Also for active scientists and engineers, updating their knowledge and understanding of the frontiers of the technology.

The emerging field of semiconductor quantum optics combines semiconductor physics and quantum optics, with the aim of developing quantum devices with unprecedented performance. In this book researchers and graduate students alike will reach a new level of understanding to begin conducting state-of-the-art investigations. The book combines theoretical methods from quantum optics and solid-state physics to give a consistent microscopic description of light-matter- and many-body-interaction effects in low-dimensional semiconductor nanostructures. It develops the systematic theory needed to treat semiconductor quantum-optical effects, such as strong light-matter coupling, light-matter entanglement, squeezing, as well as quantum-optical semiconductor spectroscopy. Detailed derivations of key equations help readers learn the techniques and nearly 300 exercises help test their understanding of the materials covered. The book is accompanied by a website hosted by the authors, containing further discussions on topical issues, latest trends and publications on the field. The link can be found at www.cambridge.org/9780521875097.

In its original form, this widely acclaimed primer on the fundamentals of quantized semiconductor structures was published as an introductory chapter in Raymond Dingle's edited volume (24) of Semiconductors and Semimetals. Having already been praised by reviewers for its excellent coverage, this material is now available in an updated and expanded "student edition." This work promises to become a standard reference in the field. It covers the basics of electronic states as well as the fundamentals of optical interactions and quantum transport in two-dimensional quantized systems. This revised student edition also includes entirely new sections discussing applications and one-dimensional and zero-dimensional systems. Available for the first time in a new, expanded version Provides a concise introduction to the fundamentals and fascinating applications of quantized semiconductor structures

This text is a first attempt to pull together the whole of semiconductor science and technology since 1970 in so far as semiconductor multilayers are concerned. Material, technology, physics and device issues are described with approximately equal emphasis, and form a single coherant point of view. The subject matter is the concern of over half of today's active semiconductor scientists and technologists, the remainder working on bulk semiconductors and devices. It is now routine to design and the prepare semiconductor multilayers at a time, with independent control over the dropping and composition in each layer. In turn these multilayers can be patterned with features that as a small as a few atomic layers in lateral extent. The resulting structures open up many new ares of exciting solid state and quantum physics. They have also led to whole new generations of electronic and optoelectronic devices whose superior performance relates back to the multilayer structures. The principles established in the field have several decades to go, advancing towards the ultimate of materials engineering, the design and preparation of solids atom by atom. The book should appeal equally to physicists, electronic engineers and materials scientists.

Low-Dimensional Semiconductor Structures offers a seamless, atoms-to-devices introduction to the latest quantum heterostructures. It covers their fabrication; electronic, optical, and transport properties; role in exploring new physical phenomena; and utilization in devices. The authors describe the epitaxial growth of semiconductors and the physical behavior of electrons and phonons in low-dimensional structures. They then go on to discuss nonlinear optics in quantum heterostructures. The final chapters deal with semiconductor lasers, mesoscopic devices, and high-speed heterostructure devices. The book contains many exercises and comprehensive references.

Narrow gap semiconductors are the most important materials for the preparation of advanced modern infrared systems. They often operate at the extremes of the rules of semiconductor science. This book offers clear descriptions of crystal growth and the fundamental structure and properties of these unique materials. Topics covered include band structure, optical and transport properties, and lattice vibrations and spectra. A thorough treatment of the properties of low-dimensional systems and their relation to infrared applications is provided.

This book contains contributions on some of the most important and current topics on the physics of low dimensional systems. The main emphasis is on the magnetic properties of surfaces, thin films, and atomic clusters. State-of-the-art techniques are discussed in detail. Techniques for the production and measurement of nanostructures are discussed, and pioneering contributions on the effect on health of these particles are presented. Important studies on semiconductor nanostructures are addressed as well as aerosol systems.

This book, Condensed Matter and Material Physics, incorporates the work of multiple authors to enhance the theoretical as well as experimental knowledge of materials. The investigation of crystalline solids is a growing need in the electronics industry. Micro and nano transistors require an in-depth understanding of semiconductors of different groups. Amorphous materials, on the other hand, as non-equilibrium materials are widely applied in sensors and other medical and industrial applications. Superconducting magnets, composite materials, lasers, and many more applications are integral parts of our daily lives. Superfluids, liquid crystals, and polymers are undergoing active research throughout the world. Hence profound information on the nature and application of various materials is in demand. This book bestows on the reader a deep knowledge of physics behind the concepts, perspectives, characteristic properties, and prospects. The book was constructed using 10 contributions from experts in diversified fields of condensed matter and material physics and its technology from over 15 research institutes across the globe.

Graduate text with comprehensive treatment of semiconductor device physics and engineering, and descriptions of real optoelectronic devices.

The purpose of this collective book is to present a non-exhaustive survey of sp- related phenomena in semiconductors with a focus on recent research. In some sense it may be regarded as an updated version of theOpticalOrientation book, which was entirely devoted to spin physics in bulk semiconductors. During the 24 years that have elapsed, we have witnessed, on the one hand, an extraordinary development in the wonderful semiconductor physics in two dim- sions with the accompanying revolutionary applications. On the other hand, during the last maybe 15 years there was a strong revival in the interest in spin phen- ena, in particular in low-dimensional semiconductor structures. While in the 1970s and 1980s the entire world population of researchers in the ?eld never exceeded 20 persons, now it can be counted by the hundreds and the number of publications by the thousands. This explosive growth is stimulated, to a large extent, by the hopes that the electron and/or nuclear spins in a semiconductor will help to accomplish the dream of factorizing large numbers by quantum computing and eventually to develop a new spin-based electronics, or “spintronics”. Whether any of this will happen or not, still remains to be seen. Anyway, these ideas have resulted in a large body of interesting and exciting research, which is a good thing by itself. The ?eld of spin physics in semiconductors is extremely rich and interesting with many spectacular effects in optics and transport.

This textbook presents the basic elements needed to understand and engage in research in semiconductor physics. It deals with elementary excitations in bulk and low-dimensional semiconductors, including quantum wells, quantum wires and quantum dots. The basic principles underlying optical nonlinearities are developed, including excitonic and many-body plasma effects. The fundamentals of optical bistability, semiconductor lasers, femtosecond excitation, optical Stark effect, semiconductor photon echo, magneto-optic effects, as well as bulk and quantum-confined Franz-Keldysh effects are covered. The material is presented in sufficient detail for graduate students and researchers who have a general background in quantum mechanics. Request Inspection Copy